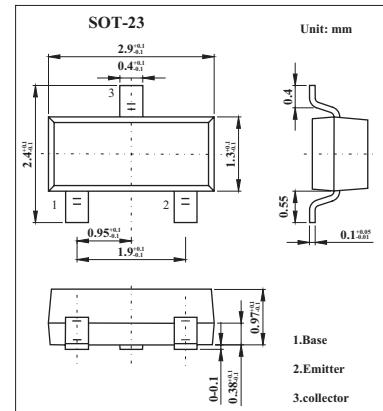


NPN Switching Transistors

BSR17A

■ Features

- High current (max. 100 mA).
- Low voltage (max. 40 V).



■ Absolute Maximum Ratings Ta = 25°C

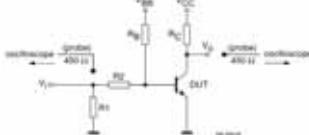
Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	100	mA
Peak collector current	I _{CM}	200	mA
Peak base current	I _{BM}	100	mA
Total power dissipation	P _{tot}	250	mW
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

BSR17A■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$I_E = 0 \text{ A}; V_{CB} = 30 \text{ V}$			50	nA
		$I_E = 0 \text{ A}; V_{CB} = 30 \text{ V}; T_j = 150^\circ\text{C}$			5	μA
Emitter cutoff current	I_{EBO}	$I_C = 0 \text{ A}; V_{EB} = 6 \text{ V}$			50	nA
DC current gain *	h_{FE}	$I_C = 10 \text{ mA}; V_{CE} = 1 \text{ V};$	100		300	
collector-emitter saturation voltage *	V_{CESat}	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA};$			200	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA};$			200	mV
base-emitter saturation voltage *	V_{BESat}	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA};$	650		850	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA};$			950	mV
Collector capacitance	C_C	$I_E = i_E = 0 \text{ A}; V_{CB} = 5 \text{ V}; f = 1 \text{ MHz}$			4	pF
Emitter capacitance	C_E	$I_C = i_C = 0 \text{ A}; V_{EB} = 500 \text{ mV}; f = 1 \text{ MHz}$			8	pF
Transition frequency	f_T	$I_C = 10 \text{ mA}; V_{CE} = 20 \text{ V}; f = 100 \text{ MHz}$	300			MHz
Noise figure	NF	$I_C = 100 \mu\text{A}; V_{CE} = 5 \text{ V}; R_S = 1 \text{ k}\Omega; f = 10 \text{ Hz to } 15.7 \text{ kHz}$			5	dB
Turn-on time	t_{on}	$I_{Con} = 10 \text{ mA}; I_{Bon} = 1 \text{ mA}; I_{Boff} = -1 \text{ mA}$			65	ns
Delay time	t_d				35	ns
Rise time	t_r				35	ns
Turn-off time	t_{off}				240	ns
Storage time	t_s				200	ns
Fall time	t_f				50	ns

* Pulse test: $t_p \leq 300 \mu\text{s}$; $d \leq 0.02$.



$V_i = 5 \text{ V}; T = 500 \mu\text{s}; t_p = 10 \mu\text{s}; t_r = t_f \leq 3 \text{ ns}.$
 $R_1 = 56 \Omega; R_2 = 2.5 \text{ k}\Omega; R_B = 3.9 \text{ k}\Omega; R_C = 270 \Omega.$
 $V_{BE} = -1.9 \text{ V}; V_{CC} = 3 \text{ V}.$
Oscilloscope input impedance $Z_i = 50 \Omega$.

■ Marking

Marking	U92 OR 54
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